

In the claims:

Claims 1-41 (canceled)

Claim 42 (currently amended) A semiconductor wafer which comprises:

a plurality of integrated circuits, each of said integrated circuits separated from the other of said integrated circuits by a scribe region at the periphery of each said integrated circuit; each of said integrated circuits including:

a centrally disposed core region;

at least one bond pad disposed between said core region and said scribe region;

an electrostatic discharge device; and

an I/O buffer disposed between said scribe region and said core region and laterally of said bond pad relative to said core region and said scribe region.-

Claim 43 (previously presented) A semiconductor wafer which comprises:

a plurality of integrated circuits, each of said integrated circuits separated from the other of said integrated circuits by a scribe region at the periphery of each said integrated circuit; each of said integrated circuits including:

a centrally disposed core region;

at least one bond pad disposed between said core region and said scribe region;

an electrostatic discharge device disposed at least partially beneath said bond pad;

and

an I/O buffer disposed between said scribe region and said core region.

Claim 44 (currently amended) The semiconductor wafer of claim 43 ~~53~~ wherein said I/O buffer is further disposed laterally of said bond pad relative to said region and said scribe region.

Claim 45 (currently amended) An integrated circuit which comprises:
a semiconductor substrate which includes a scribe at the periphery of said substrate and a centrally disposed core region;
at least one bond pad disposed between said core region and said scribe region;
an electrostatic discharge device; and
an I/O buffer disposed between said scribe region and said core region and laterally of said bond pad relative to said core region and said scribe region.-

Claim 46 (previously presented) An integrated circuit which comprises:
a semiconductor substrate which includes a scribe at the periphery of said substrate and a centrally disposed core region;
at least one bond pad disposed between said core region and said scribe region;
an electrostatic discharge device disposed at least partially beneath said bond pad;
and
an I/O buffer disposed between said scribe region and said core region.

47. (currently amended)) The circuit of claim 46 ~~56~~ wherein said I/O buffer is further disposed laterally of said bond pad relative to said core region and said scribe region.

Claim 48 (currently amended) A method of fabricating a semiconductor wafer which comprises the steps of:

providing a plurality of integrated circuits, each of said integrated circuits separated from the other of said integrated circuits by a scribe region at the periphery of each said integrated circuit; and providing in each of said integrated circuits:

- a centrally disposed core region;
- at least one bond pad disposed between said core region and said scribe region;
- an electrostatic discharge device; and
- an I/O buffer disposed between said scribe region and said core region and laterally of said bond pad relative to said core region and said scribe region.-

Claim 49 (previously presented) A method of fabricating a semiconductor wafer which comprises the steps of:

providing a plurality of integrated circuits, each of said integrated circuits separated from the other of said integrated circuits by a scribe region at the periphery of each said integrated circuit; and providing in each of said integrated circuits:

- a centrally disposed core region;
 - at least one bond pad disposed between said core region and said scribe region;
 - an electrostatic discharge device disposed at least partially beneath said bond pad;
- and
- an I/O buffer disposed between said scribe region and said core region.

Claim 50. (currently amended) The method of claim ~~49~~ 59 wherein said I/O buffer is further disposed laterally of said bond pad relative to said core region and said scribe region.

Claim 51 (currently amended) A method of fabricating an integrated circuit which comprises the steps of:

- providing a semiconductor substrate which includes a scribe at the periphery of said substrate and a centrally disposed core region;

- providing at least one bond pad disposed between said core region and said scribe region;

- providing a electrostatic discharge device; and

- providing an I/O buffer disposed between said scribe region and said core region and laterally of said bond pad relative to said core region and said scribe region.;

Claim 52 (previously presented) A method of fabricating an integrated circuit which comprises the steps of:

- providing a semiconductor substrate which includes a scribe at the periphery of said substrate and a centrally disposed core region;

- providing at least one bond pad disposed between said core region and said scribe region;

- providing a electrostatic discharge device disposed at least partially beneath said bond pad; and

- providing an I/O buffer disposed between said scribe region and said core region.

Claim 53 (currently amended) The method of claim 52 ~~62~~ wherein said I/O buffer is further disposed laterally of said bond pad relative to said core region and said scribe region.